PNP 500mA 30V General purpose transistors

Datasheet

Parameter	Value
V _{CEO}	-30V
I _C	-0.5A

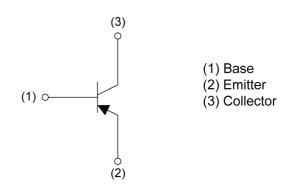
Outline

EMT3F	UMT3F
(1) (2)	(1)
2SAR502EB	2SAR502UB
SOT-416FL	SOT-323FL

Features

- 1)General purpose.
- 2)Complementary NPN types: 2SCR502EB(EMT3F)/2SCR502UB(UMT3F)
- 3)Collector current is large.
- 4)Low V_{CE(sat)}.

•Inner circuit



Application

LOW FREQUENCY AMPLIFIER

Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SAR502EB	EMT3F	1616	TL	180	8	3000	LT
2SAR502UB	UMT3F	2021	TL	180	8	3000	LT

● Absolute maximum ratings (T_a = 25°C)

Parameter			Symbol	Values	Unit	
Collector-base voltage			V_{CBO}	-30	V	
Collector-emitter voltage			V _{CEO}	-30	V	
Emitter-base voltage				-6	V	
			I _C *1	-0.5	Α	
Collector current	Collector current			-1	Α	
Base current			I _B	-0.15	Α	
Down disaination	2SAR502EB		D *3	150	\^/	
Power dissipation 2SAR502UB		P _D *3	200	mW		
Junction temperature			Tj	150	°C	
Range of storage temperature			T _{stg}	-55 to +150	°C	

● Electrical characteristics (T_a = 25°C)

Davameter	Cymabal	Conditions	Values			Lloit
Parameter	Symbol Conditions —		Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV _{CBO}	I _C = -100μA	-30	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = -1mA	-30	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = -100μA	-6	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = -25V	-	-	-200	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V	-	-	-200	nA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -200mA, I _B = -10mA	-	-150	-400	mV
DC current gain	h _{FE}	$V_{CE} = -2V, I_{C} = -100 \text{mA}$	200	-	500	-
Transition frequency	f _T *4	V _{CE} = -10V, I _E = 100mA, f = 100MHz	-	520	-	MHz
Output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0A, f = 1MHz	-	4	-	pF

^{*1} Limited by power dissipation.

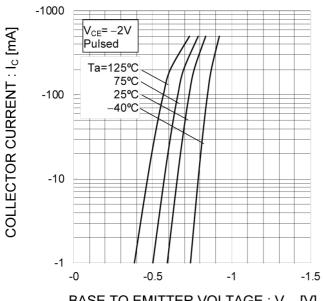
^{*2} Pw=10ms, Single pulse.

^{*3} Each terminal mounted on a reference land.

^{*4} Pulsed

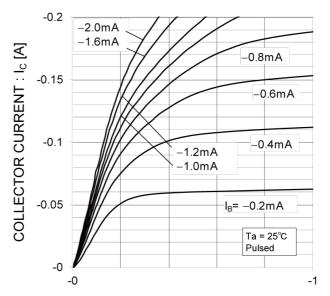
● Electrical characteristic curves(T_a = 25°C)

Fig.1 Grounded Emitter Propagation Characteristics



BASE TO EMITTER VOLTAGE: VBE [V]

Fig.2 Typical Output Characteristics



COLLECTOR TO EMITTER VOLTAGE: VCE [V]

Fig.3 DC Current Gain vs. Collector Current(I)

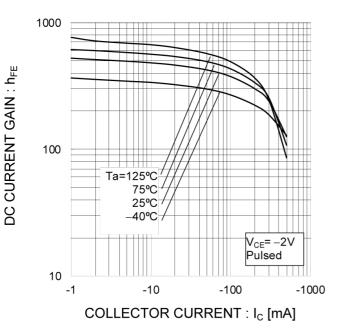
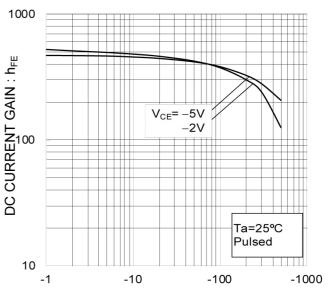


Fig.4 DC Current Gain vs. Collector Current(II)



COLLECTOR CURRENT : I_C [mA]

● Electrical characteristic curves(T_a = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current(I)

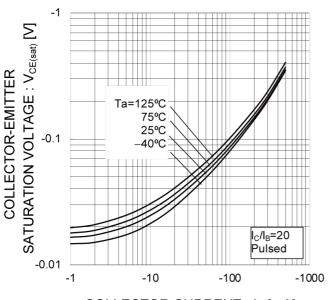
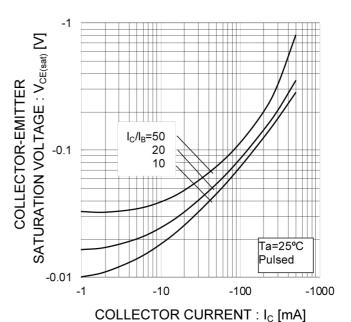


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current(II)



COLLECTOR CURRENT: Ic [mA]

Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

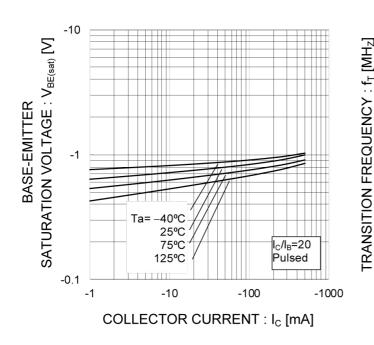
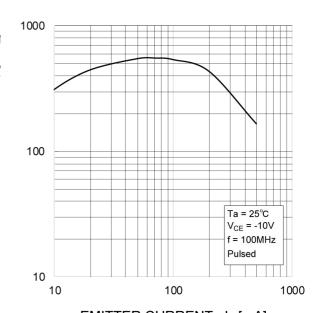


Fig.8 Gain Bandwidth Product vs. Emitter Current



EMITTER CURRENT : I_E [mA]

● Electrical characteristic curves(T_a = 25°C)

Fig.9 Emitter input capacitance vs. Emitter-Base Voltage Collector output capacitance vs. Collector-Base Voltage

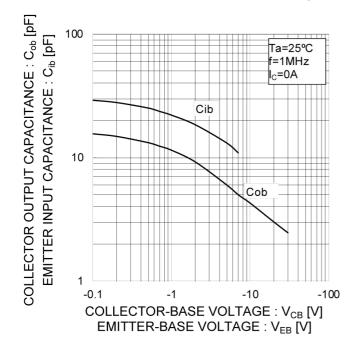


Fig.10 Safe Operating Area

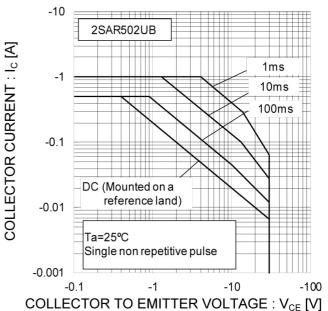
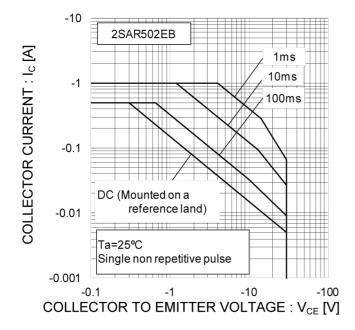
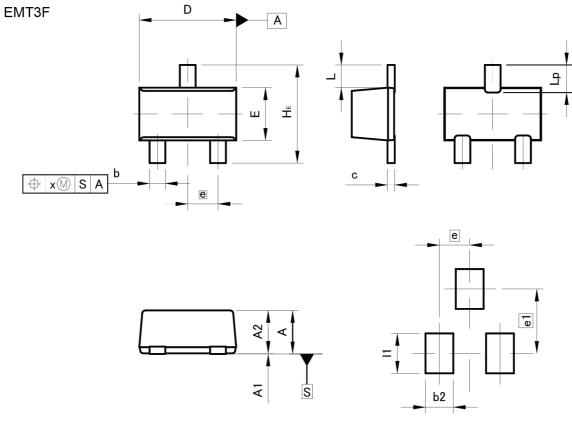


Fig.11 Safe Operating Area



Dimensions



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

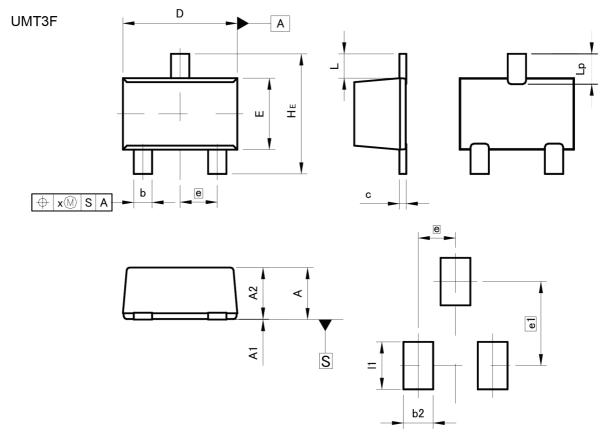
DIM	MILIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	0.65	0.85	0.026	0.033
A1	0.00	0.10	0.000	0.004
A2	0.60	0.80	0.024	0.031
b	0.21	0.36	0.008	0.014
С	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
Е	0.76	0.96	0.030	0.038
е	0.5	50	0.020	
HE	1.50	1.70	0.059	0.067
L	0.3	37	0.0	115
Lp	0.35	0.55	0.014	0.022
х	_	0.10	_	0.004

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
b2	-	0.46	I	0.018	
e1	_	1.05	-	0.041	
I 1	1	0.65	I	0.026	

Dimension in mm/inches



Dimensions



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	0.85	1.05	0.033	0.041
A1	0.00	0.10	0.000	0.004
A2	0.80	1.00	0.031	0.039
b	0.27	0.42	0.011	0.017
С	0.08	0.18	0.003	0.007
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.0	65	0.0	26
HE	2.00	2.20	0.079	0.087
L	0.4	43	0.0	17
Lp	0.43	0.63	0.017	0.025
х	_	0.10	_	0.004

	DIM	MILIMETERS		INCHES		
DIM		MIN	MAX	MIN	MAX	
	b2	ı	0.52	I	0.020	
	e1	1.4	47	0.0	58	
	l1	- 0.83		I	0.033	

Dimension in mm/inches



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